

ECE601 | Advanced Analog Integrated Circuits

Band gap & Constant current Cores

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Task

Design a constant VBG across PVT and also a digitally-programmable $100\mu\text{A}$ ($T=25^\circ\text{C}$) PTAT current using 2bits.

Spec.	Target	Units	Comments
Temperature range	-40 to +125	Co	
Supply Variation	-10 to +10	%	From the nominal supply value
Process Corners	TT, SS, FF		
Nominal VBG Voltage	0.5	V	
Worst case ΔVBG across Temperature	± 1	%	For TT Corner
Worst case ΔVBG across supply	± 0.5	%	
Worst case ΔVBG	± 3	%	Across PVT
Worst case ΔVBG sigma across MC	± 1	%	For TT Corner
Nominal IPTAT Current	100	μA	@ 25° , Across PV
IPTAT Slope accuracy	--	%	Across PVT and 4 Setting
IPTAT Slope step	-12.5	%	Across PVT
IPTAT Min Slope	-50	%	Across PVT
Worst case ΔIPTAT across supply	± 1		
Worst case ΔIPTAT	± 3		Across PVT
Worst case ΔVBG sigma across MC	± 1		For TT Corner
loop PMs	$> 60^\circ$	Deg	Across PVT
Startup Current	--	μA	Across PVT
Supply voltage	1.2	V	
Power consumption	--	mW	

Concept Design Review

Why we need a reference?

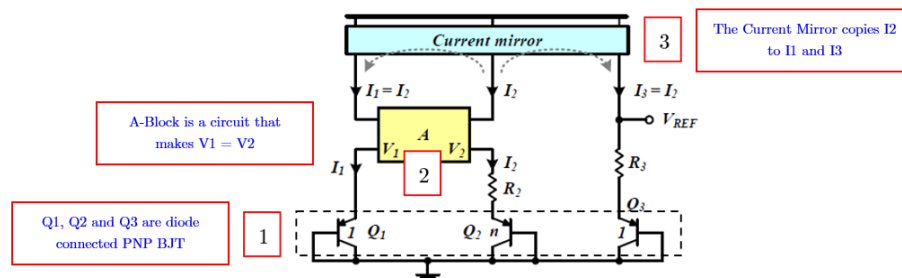
- Reference voltage generators are critical components in analog circuits, generators are required to be stabilized over process variations (P) and voltage changes (V) and Temperature changes (T)
- Poor man's reference: using voltage divider $V_{\text{ref}} = \frac{R_2}{R_1 + R_2} \times V_{\text{DD}}$.. good design makes Vref independent of P and T, but it still depends on VDD for absolute value and variations
- Bandgap Reference solve this and generate a stable reference over PVT

Temperature Coefficients

- Positive temperature coefficient (+ ve TC): Proportional to absolute temperature $\rightarrow X_{\text{PTAT}} = a \times T$
- Negative temperature coefficient (- ve TC): Complementary to absolute temperature $\rightarrow X_{\text{CTAT}} = C - b \times T$
- Zero temperature coefficient (zero TC): Temperature independent PTAT + CTAT

Basic operation

- BGR consists of 3 main parts



- Q2 is (n) BJTs diode connected in parallel $\rightarrow I_{C1} = I_1$ and $I_{C2} = I_2/n \rightarrow \therefore V_{BE1} \neq V_{BE2} \rightarrow$ there's ΔV_{BE}
- $|V_{BE}| = V_T \ln I_C/I_S \rightarrow \Delta V_{BE} = KT/q \ln n \rightarrow I_2 = \frac{\Delta V_{BE}}{R_2} = \frac{KT}{q} \ln n \times \frac{1}{R_2} \rightarrow I_2$ will have PTAT characteristics and so I_3 will be
- It can be shown that $|V_{BE}| = V_T \ln \frac{I_C}{I_S} = V_{G0} - b_1 T$ is a CTAT although I_C and V_T are PTAT but I_S is a strong function of temperature, **Why?**

$$I_S \propto \mu k T n_i^2 \text{ and } \mu (\text{mobility of holes}) \propto \mu_0 T^m, m \approx -\frac{3}{2} \text{ and } n_i^2 (\text{intrinsic carriers}) \propto T^3 e^{-\frac{E_g(\text{bandgap energy})}{KT}}$$

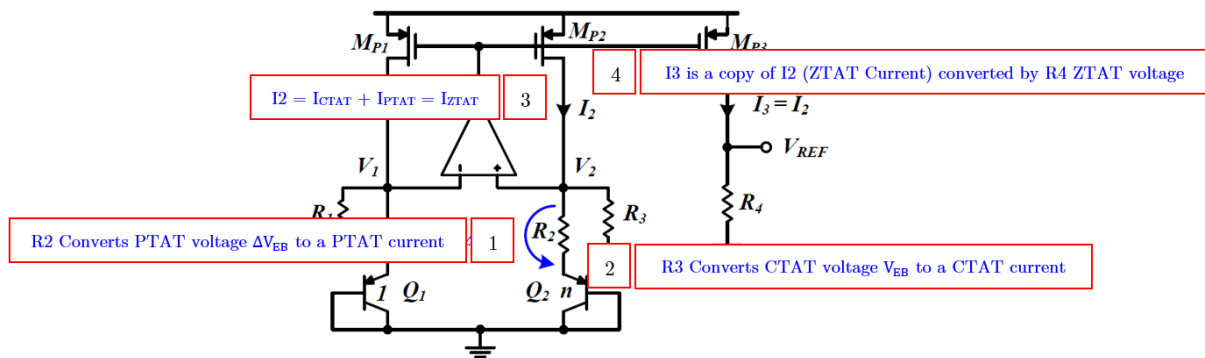
$$I_S \propto \mu_0 \times T^{m+4} \times K \times e^{-\frac{E_g(\text{bandgap energy})}{KT}}$$

$$I_S = b \times T^{m+4} \times e^{-\frac{E_g(\text{bandgap energy})}{KT}} \rightarrow \text{Strong function of Temperature} \rightarrow |V_{BE}| \text{ is CTAT}$$

$$V_{ref} = V_{R3} + V_{BE3} = a_1 \times T + V_{G0} - b_1 \times T = V_{G0} \text{ (if } a_1 = b_1 \text{)}$$

$$V_{G0} = \frac{E_g}{q} \rightarrow \text{Bandgap voltage, it's constant} = 1.2V \text{ at zero Kelvin}$$

Sub-1V BGR



BGR Stability

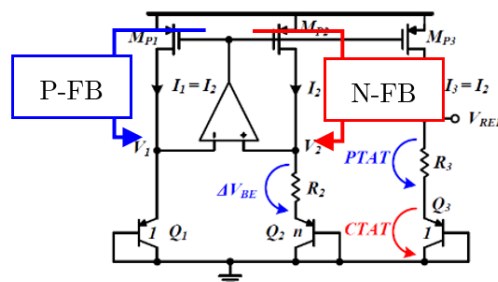
Negative or Positive Feedback?

Both Negative and Positive Feedback loop are exist so, we must guarantee $B_N > B_P$

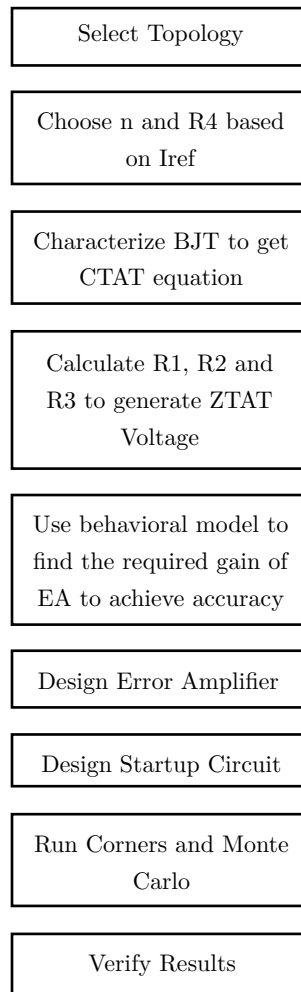
$$B_N = g_{mP2}(R_2 + 1/g_{mQ})$$

$$B_P = g_{mP1}(1/g_{mQ})$$

As R_2 is always +ve Value so, $B_N > B_P$

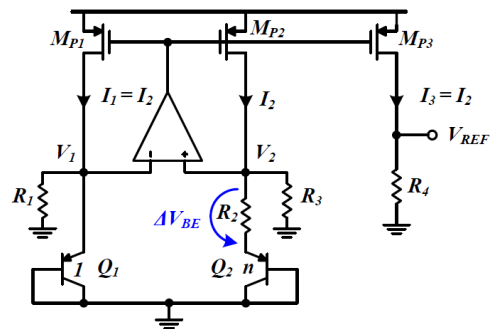


Design Flow



1. ZTAT behavior can be achieved by adding PTAT and CTAT via two approaches:
 - Currents summation approach.
 - Voltage summation approach.

Voltage approach can not achieve reference voltage lower than 1.2V, on the other side, current approach can achieve sub1V references, So we will use current



2. Choose n and R4

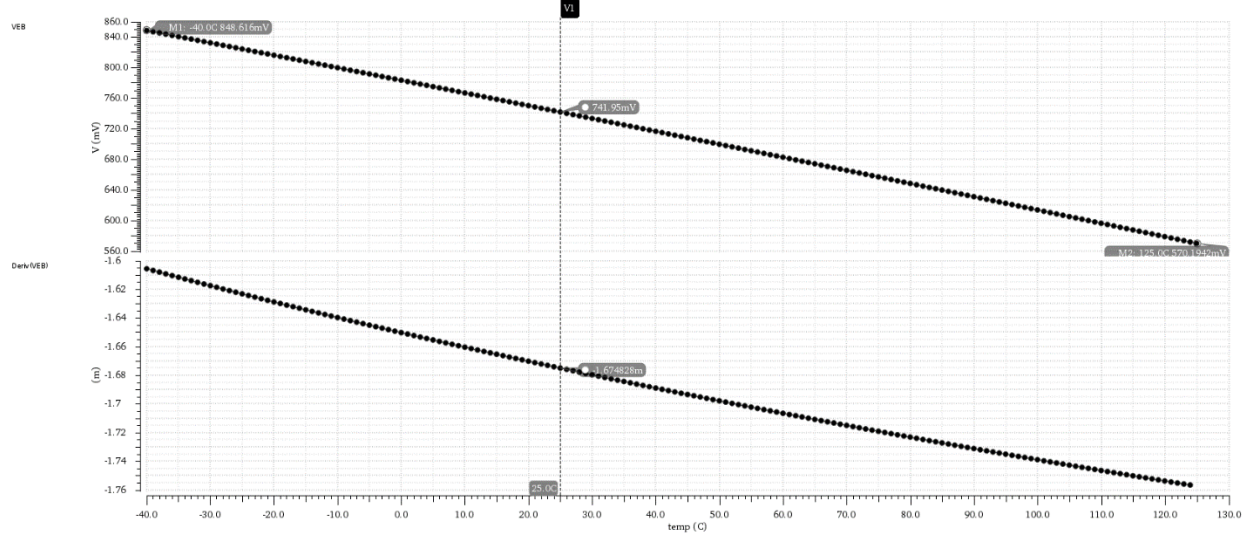
- Choice of n : Due to layout considerations two values of n are usually used, 8 which gives better matching in layout and area and 24 which gives better precision (better ΔV_{BE}), I choose n = 24 to get small offset
- Since no constrain on power consumption, I prefer choosing low ID to get low variation in PTAT and CTAT and low power consumption which make it suitable for modern applications.
- Assume $I_3 = 20 \mu A \rightarrow V_{ref} = 0.5 V \rightarrow R_4 = 25 k\Omega$, Current mirrored with same ratio so, $I_1 = I_2 = I_3 = 20 \mu A$

3. BJT Characterization

- Characterizing BJT using simple diode connected TB gives CTAT equation that helps to find R1, R2, and R3

DC Analysis 'dc' temp = (125 C -> -40 C)

1



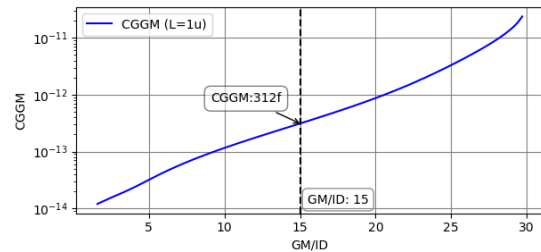
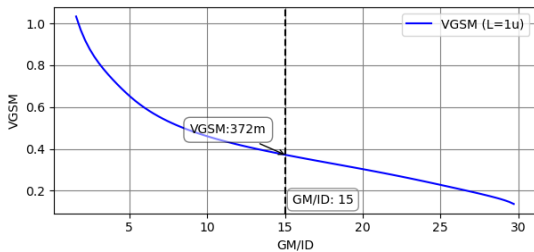
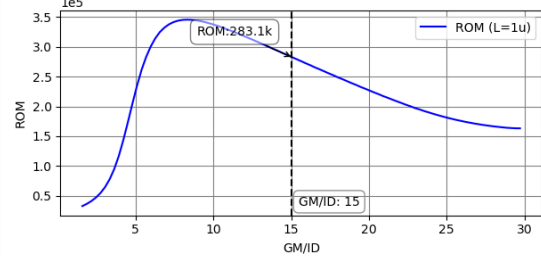
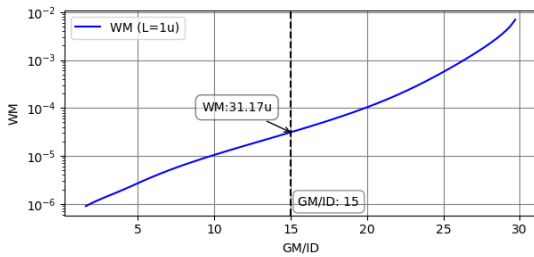
$$V_{BE} = 1.2375 - 1.675m \times T \quad \text{where (T in Kelvin)}$$

4. Calculate R1, R2 and R3

- $V_{ref} = I_3 R_4 = I_2 R_4 = R_4 \left(\frac{V_{BE1}}{R_3} + \frac{V_T \ln n}{R_2} \right) = \frac{1.2375 \times R_4}{R_3} + \frac{KT \ln n \times R_4}{q \times R_2} - \frac{1.675m \times T \times R_4}{R_3}$
- From previous equation we need $\frac{K \ln n}{q \times R_2} = \frac{1.675m}{R_3} \rightarrow (2)$ and $\frac{1.2375 \times R_4}{R_3} = 0.5 \rightarrow (3)$
- From (3) $\therefore R_4 = 25K \text{ Ohm} \rightarrow R_3 = 61.875K \text{ Ohm} = R_1 \rightarrow$ Substituting in (2) $R_2 = 10.117K \text{ Ohm}$

5. Design of the Current Mirrors

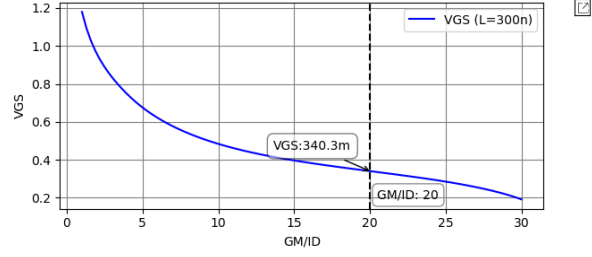
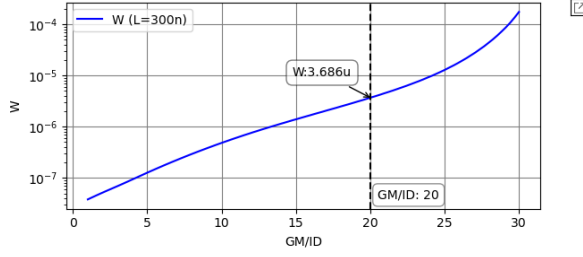
- Use Large L ($\geq 1\mu m$) is usually used so Use $L = 1 \mu m$ and $\frac{g_m}{I_D} = 15 \rightarrow$ using gm/ID charts



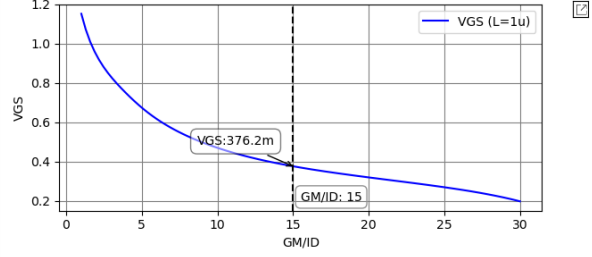
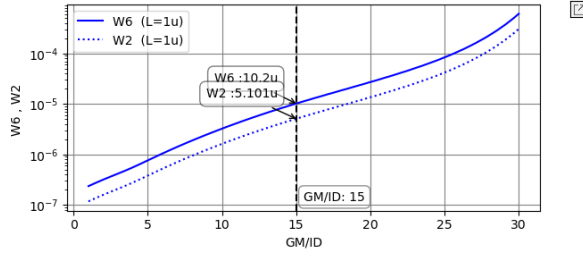
6. Design of the EA, I Choose SE Folded Cascode OTA

- Assume total current for OTA equals 40 uA and it is divided equally between the two branches

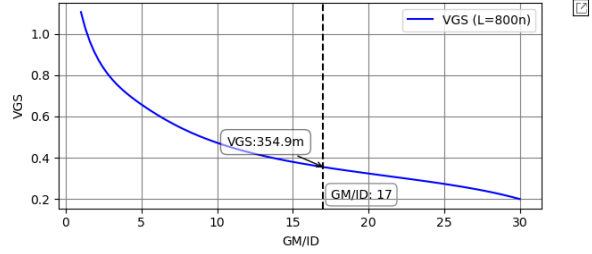
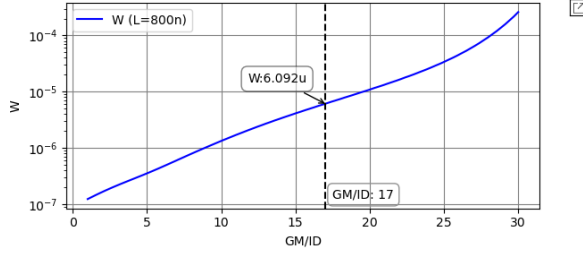
- M1 $\rightarrow L = 0.3 \mu\text{m}$ and $g_m/I_D = 20$



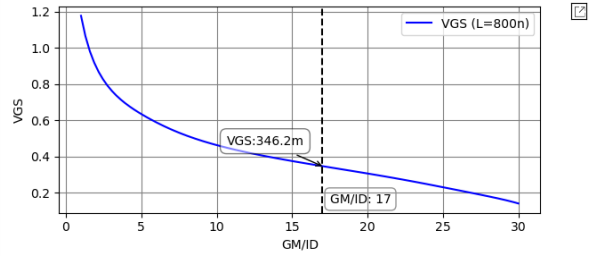
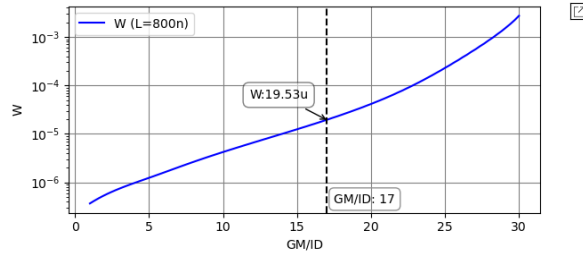
- M2 and M6 $\rightarrow L = 1 \mu\text{m}$ and $g_m/I_D = 15$



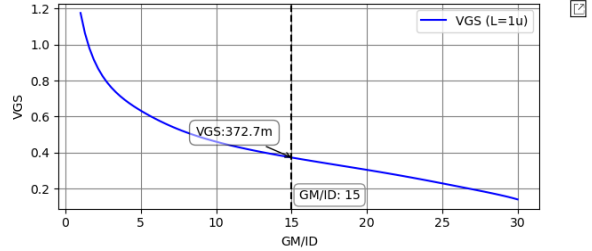
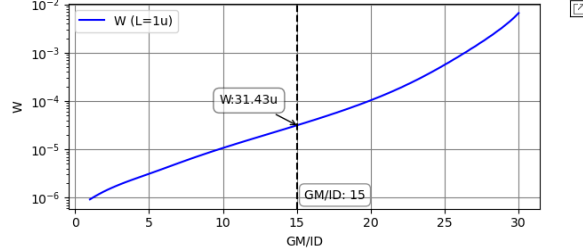
- M3 $\rightarrow L = 0.8 \mu\text{m}$ and $g_m/I_D = 17$



- M4 $\rightarrow L = 0.8 \mu\text{m}$ and $g_m/I_D = 17$

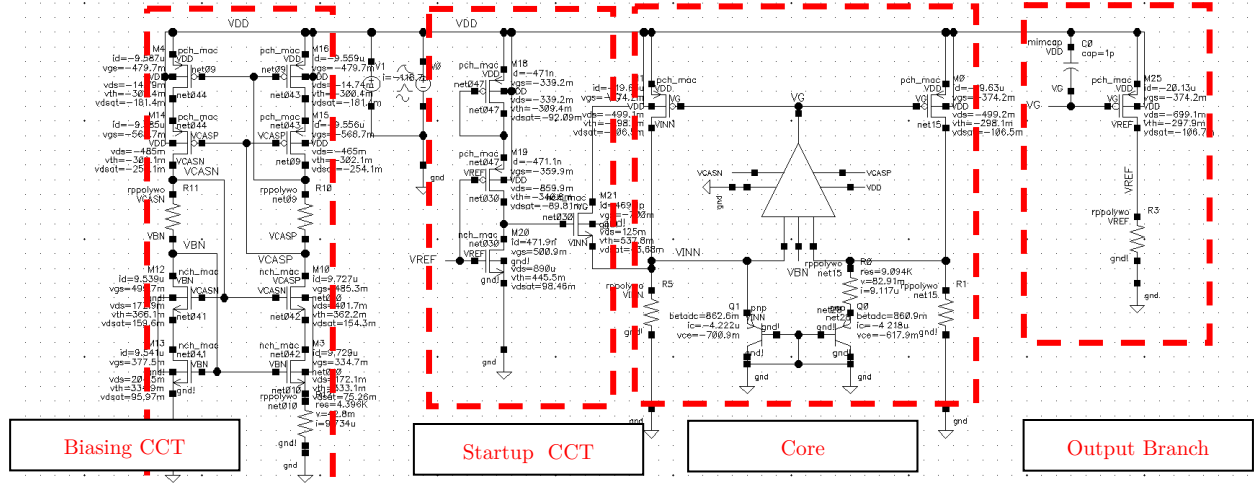


- M5 $\rightarrow L = 1 \mu\text{m}$ and $g_m/I_D = 15$

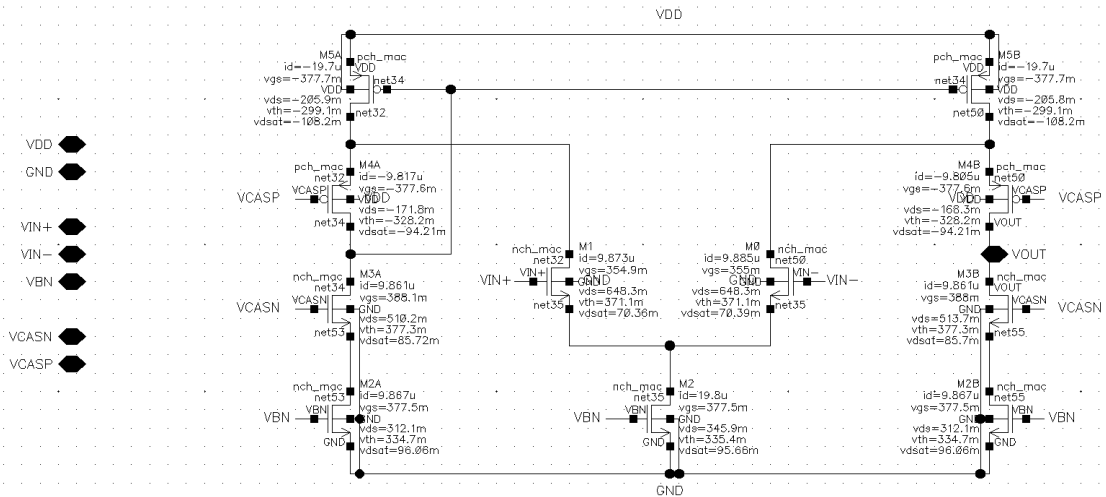


7. BGR

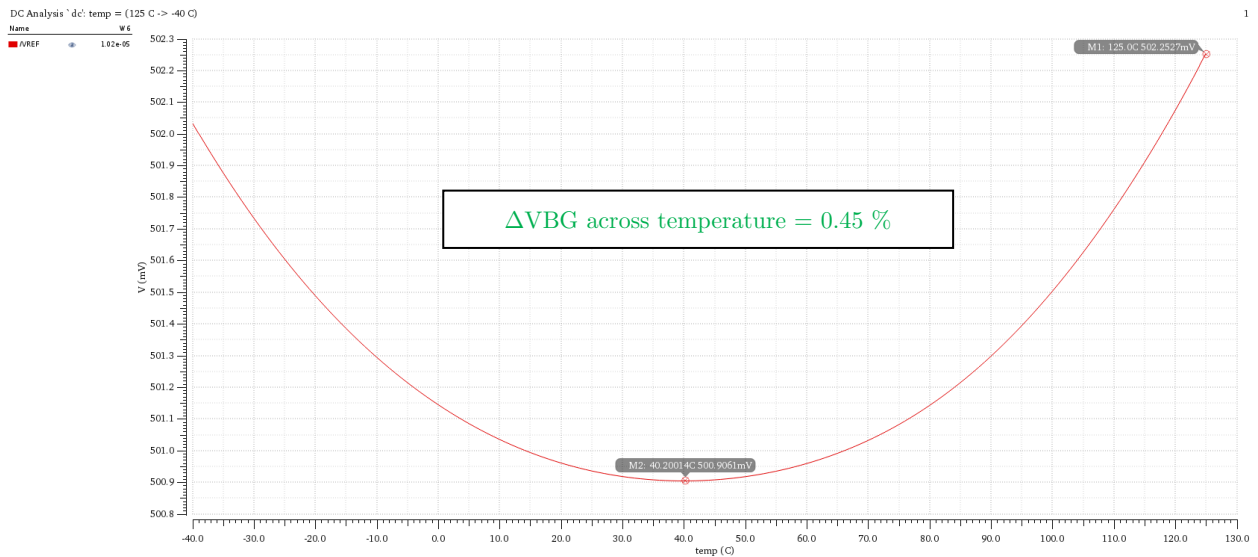
- DC operating points



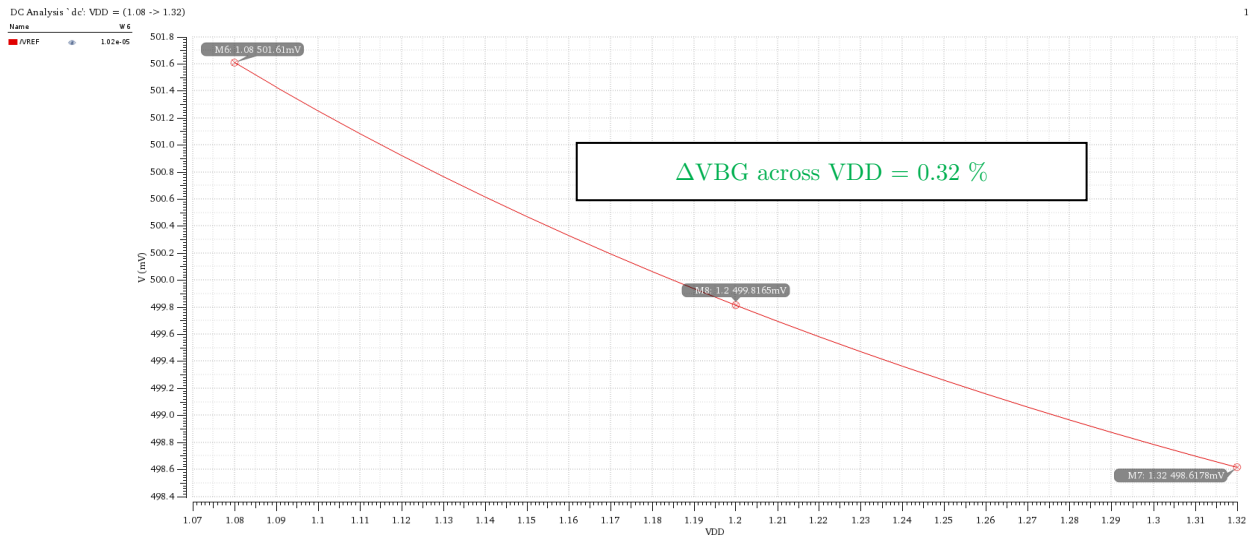
- OP Amo Operating Points



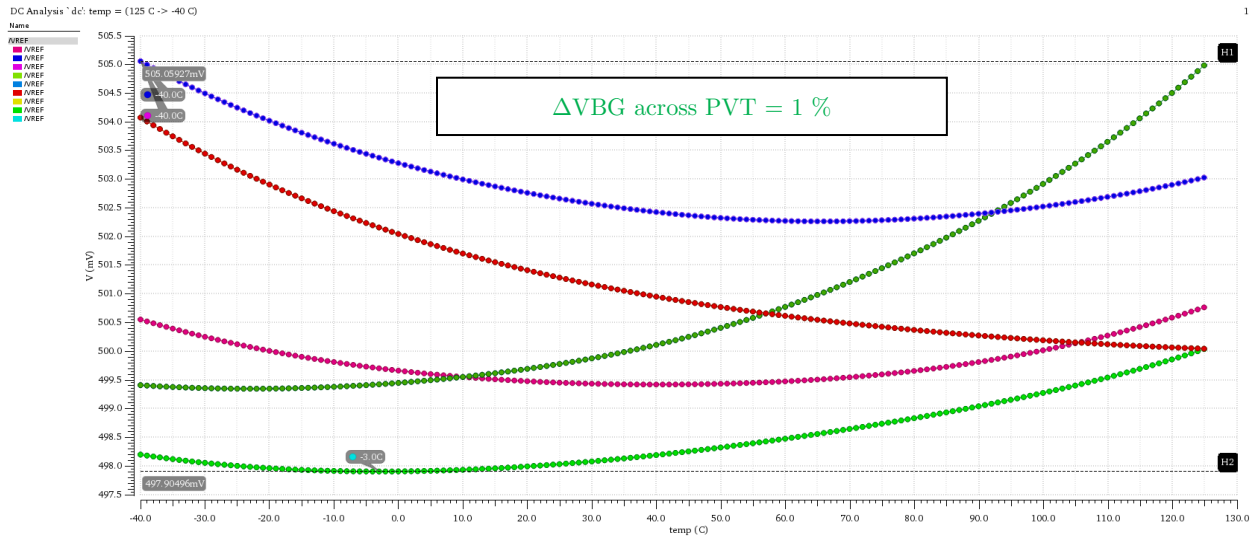
- VREF Vs Temp @ Nominal



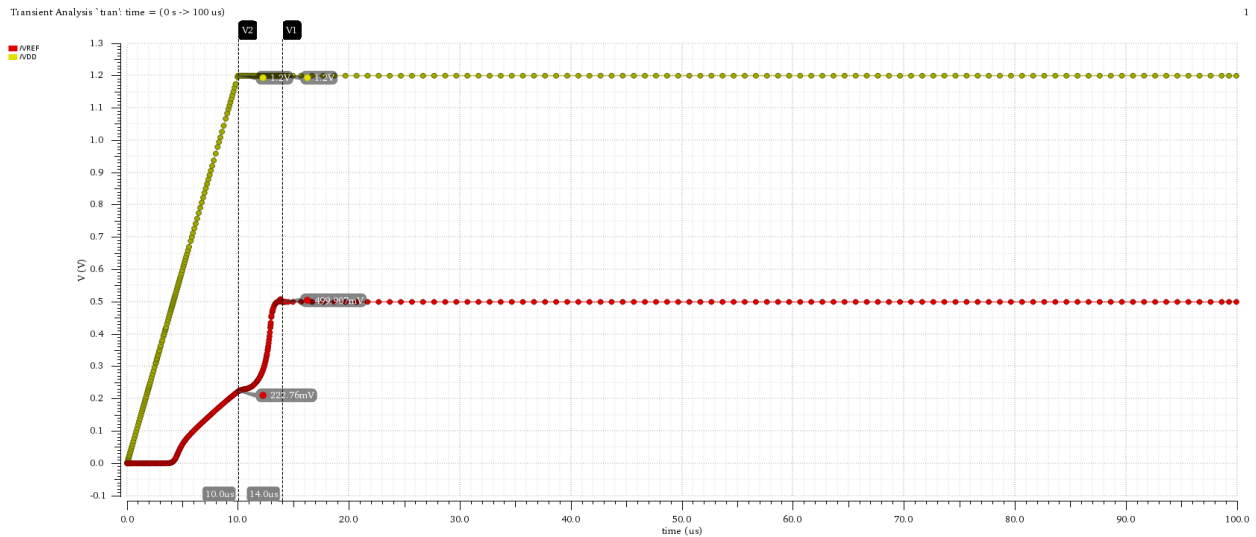
- VREF Vs VDD @ Nominal



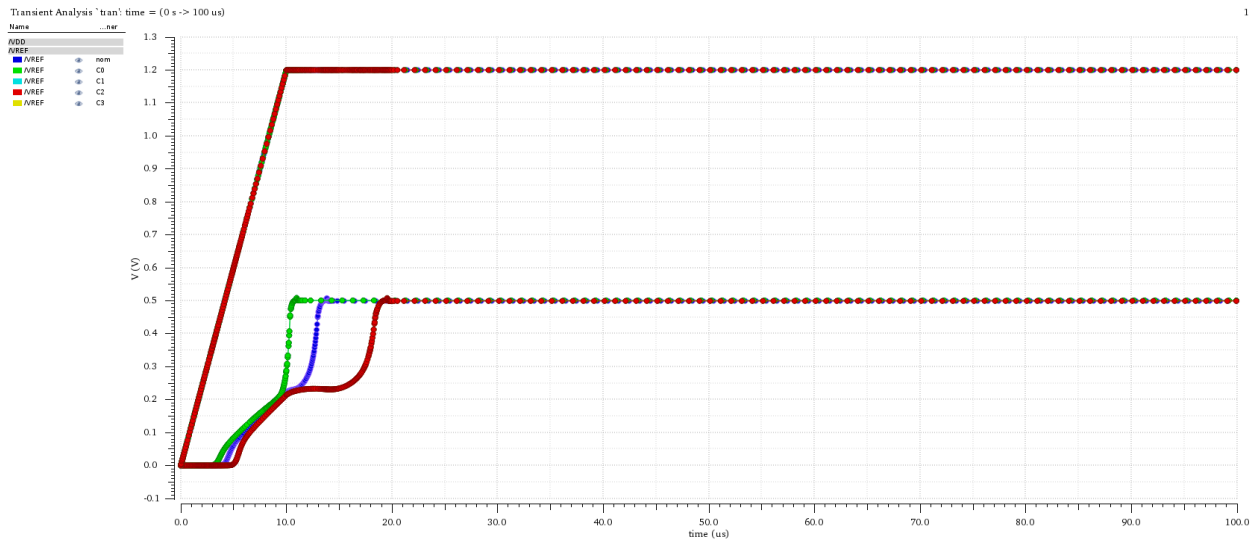
- VREF Vs Temp @ Corners



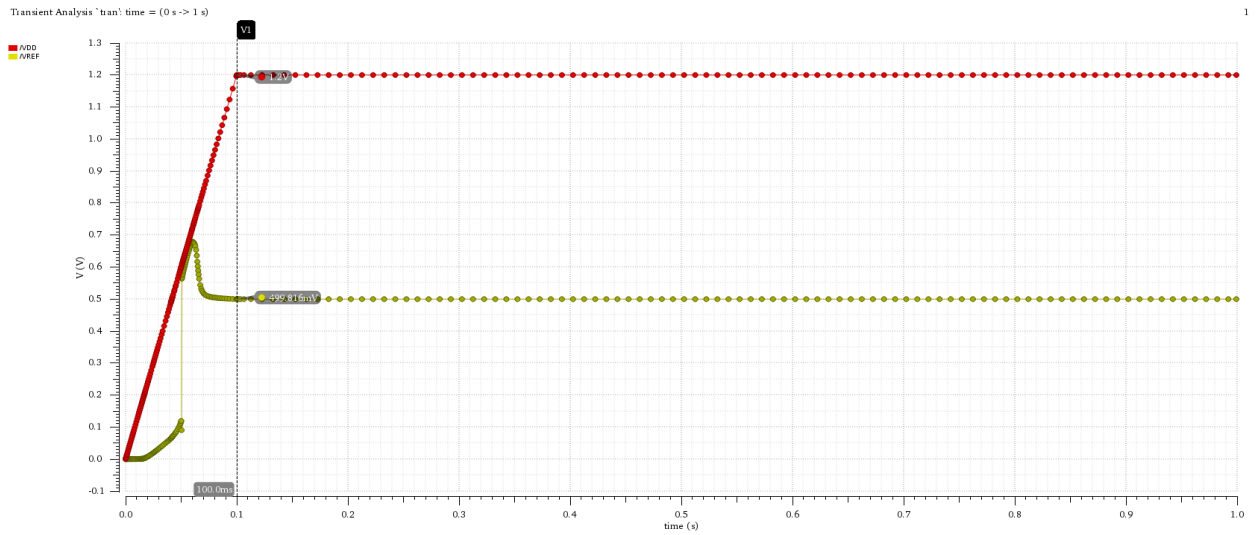
- VREF vs time (10us supply ramping) @ Nominal:



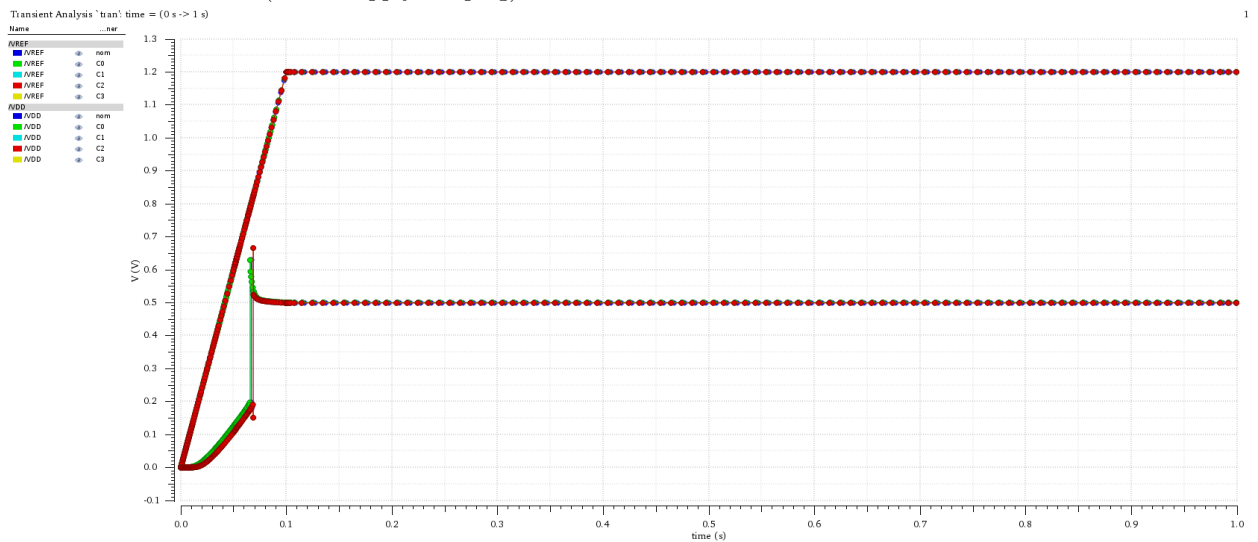
- VREF vs time (10us supply ramping) @ Corners:



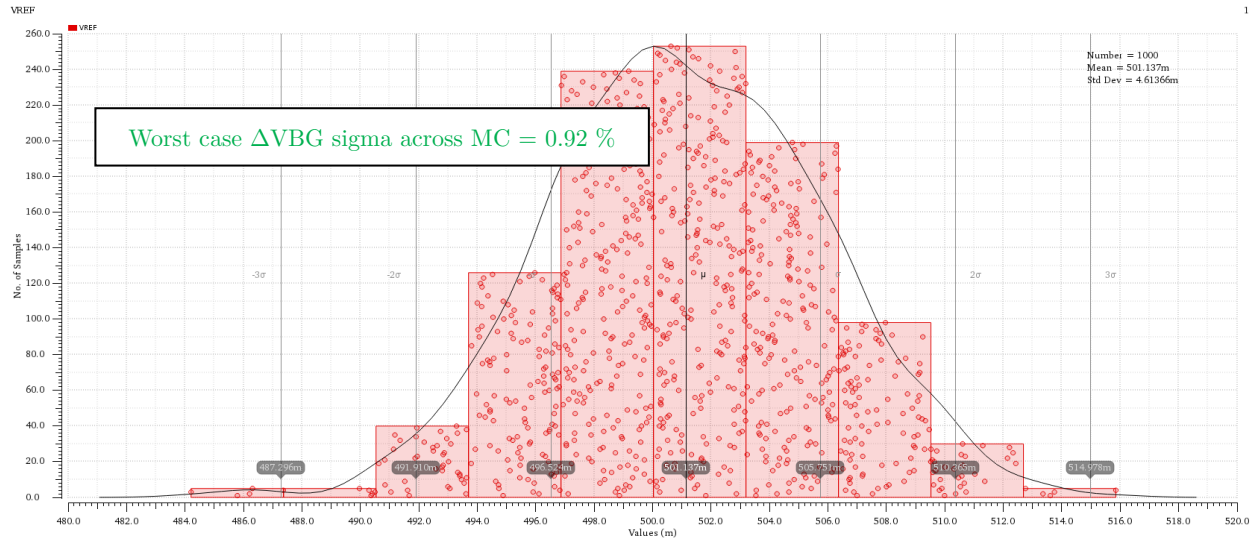
- VREF vs time (100ms supply ramping) @ Nominal:



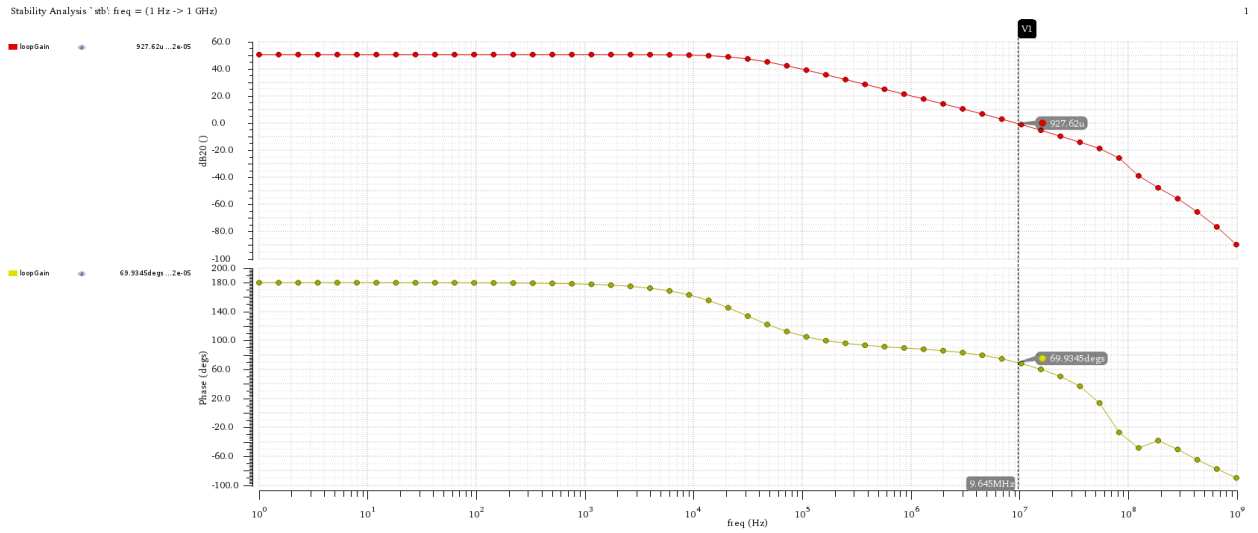
- VREF vs time (100ms supply ramping) @ Corners:



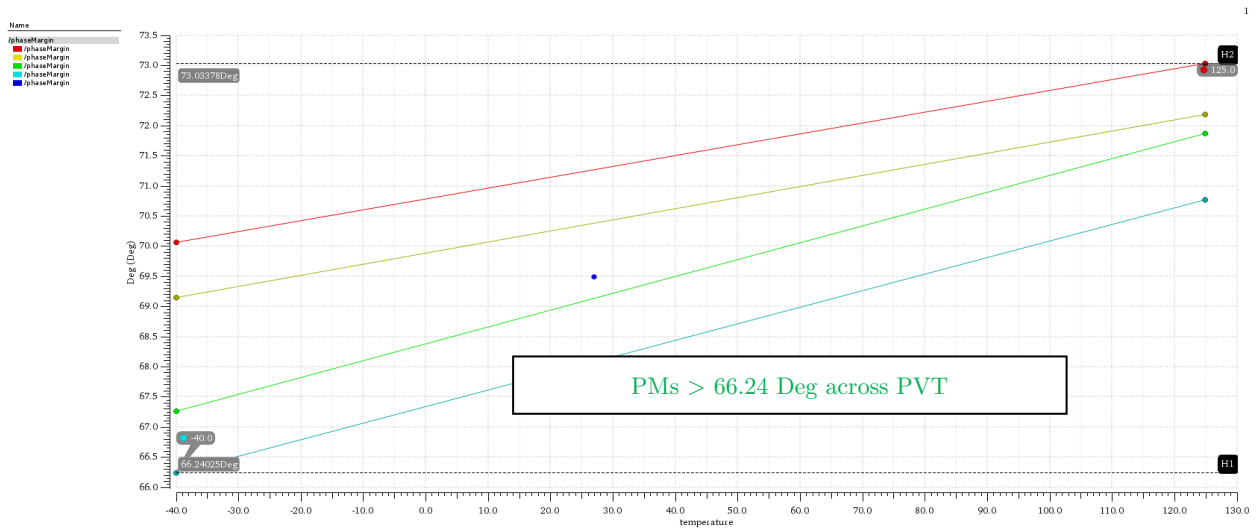
MC Results



STB @ Nominal

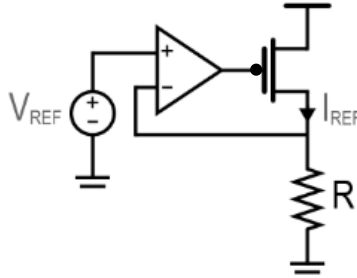


STB @ Corners

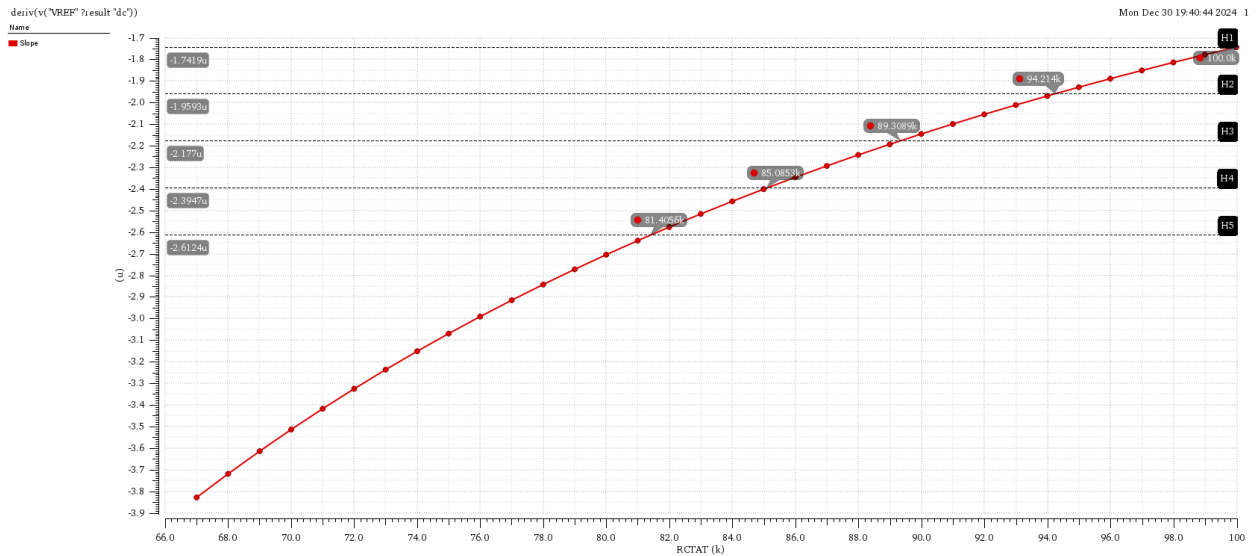


8. PTAT Current Generator

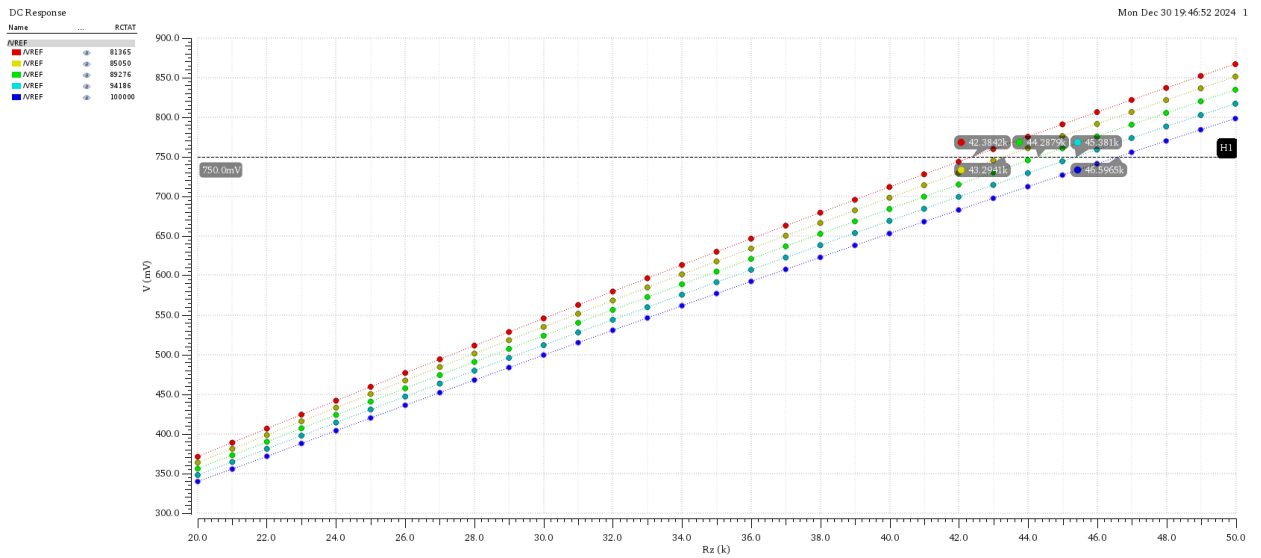
- We intentionally make V_{REF} a PTAT voltage and generate a PTAT current from it using shown circuit



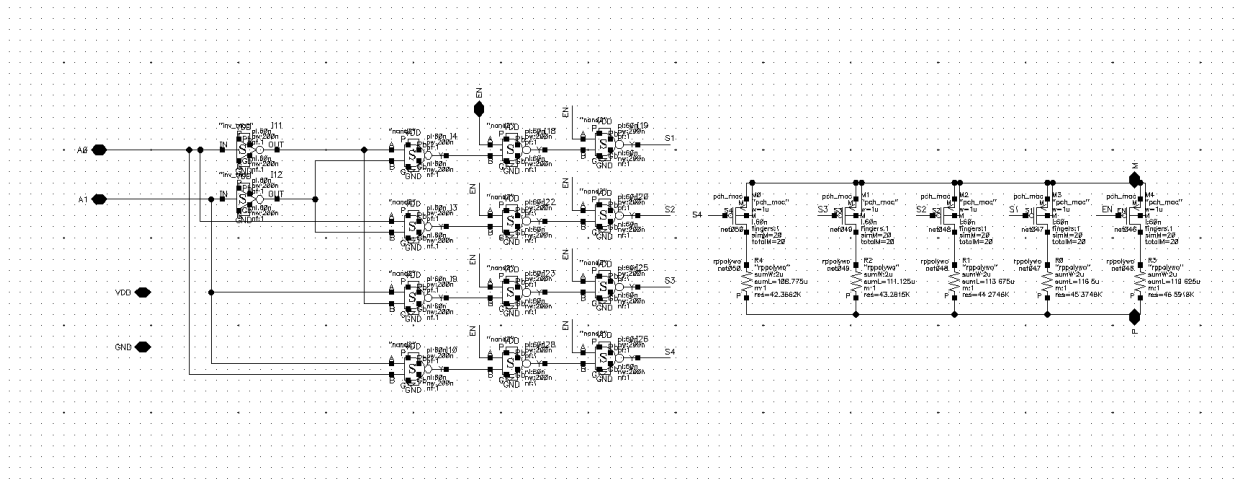
- The PTAT slope is controlled by the R_{ctat} of the BGR core so, we get the max slope of the V_{ref} Vs R_{ctat} and determine the required R_{ctat} to get the 12.5% step from it



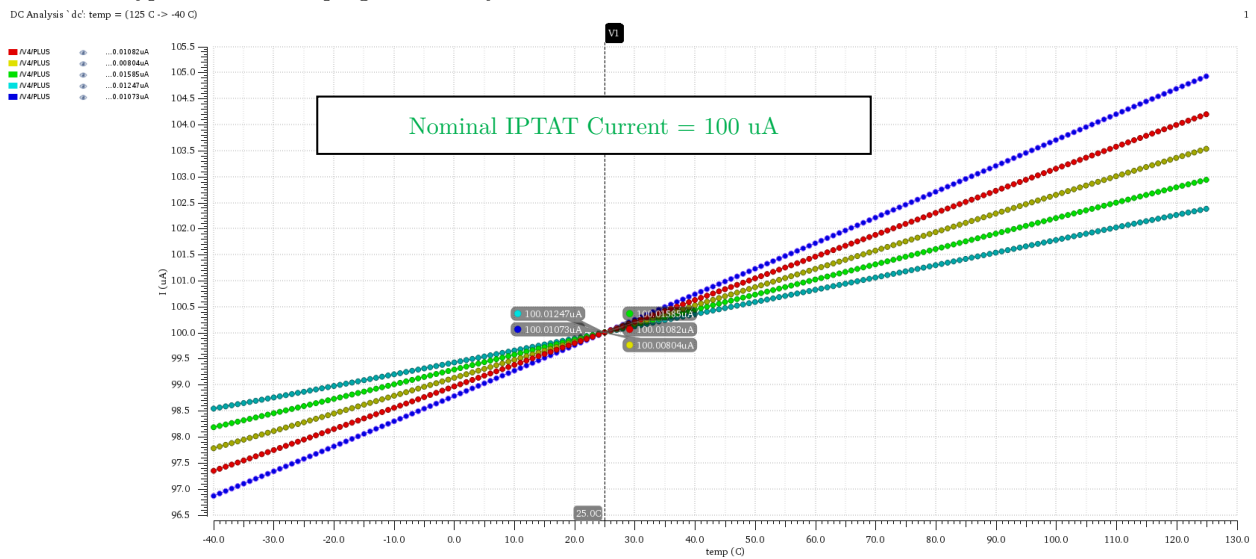
- In order to maintain the V_{ref} constant the output resistance will be also variable, so sweeping the R_{out} to maintain the output $V_{ref} = 750$ mV, we can find the required R_{out} at each step



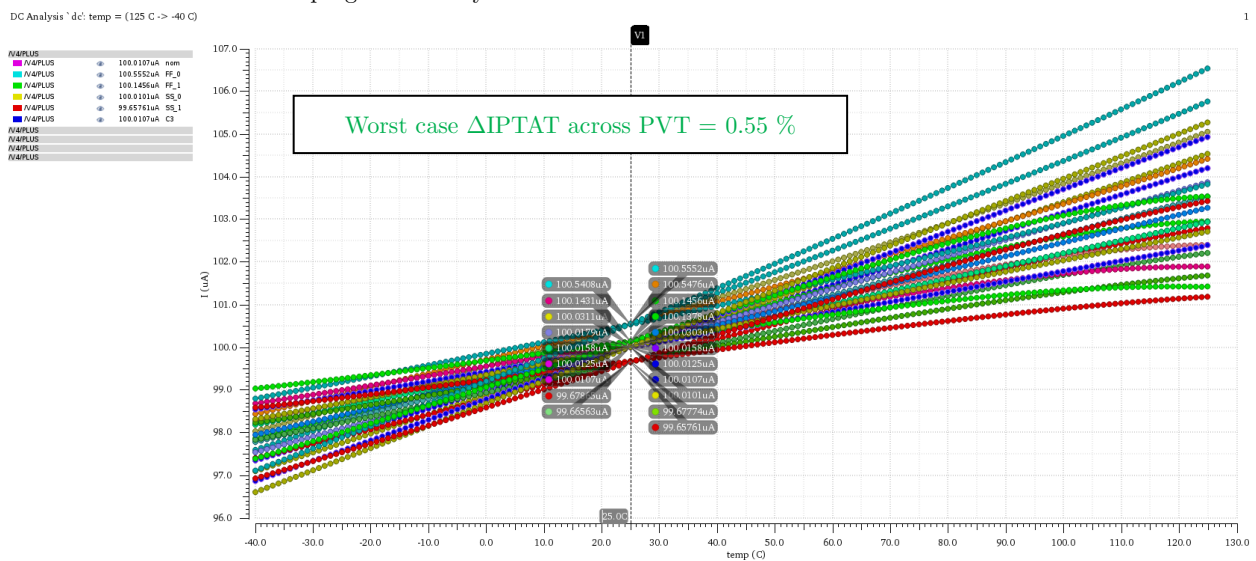
- Making the following selector to get the required R at each step with 2 bits A0 and A1 and Enable pin



- Typical Results Vs programmability

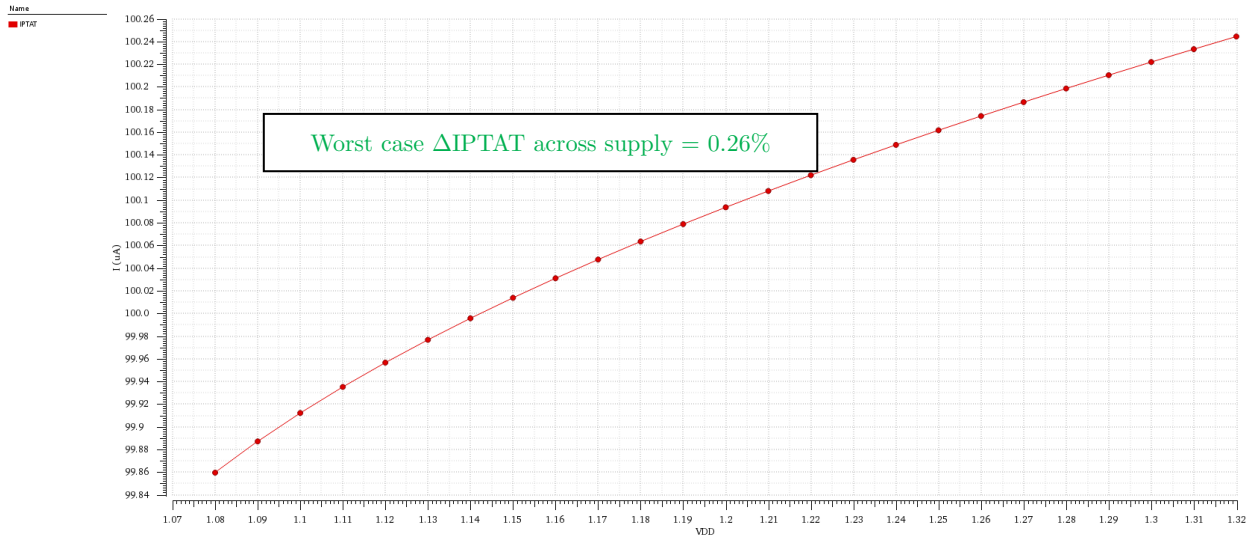


- Corners Results Vs programmability

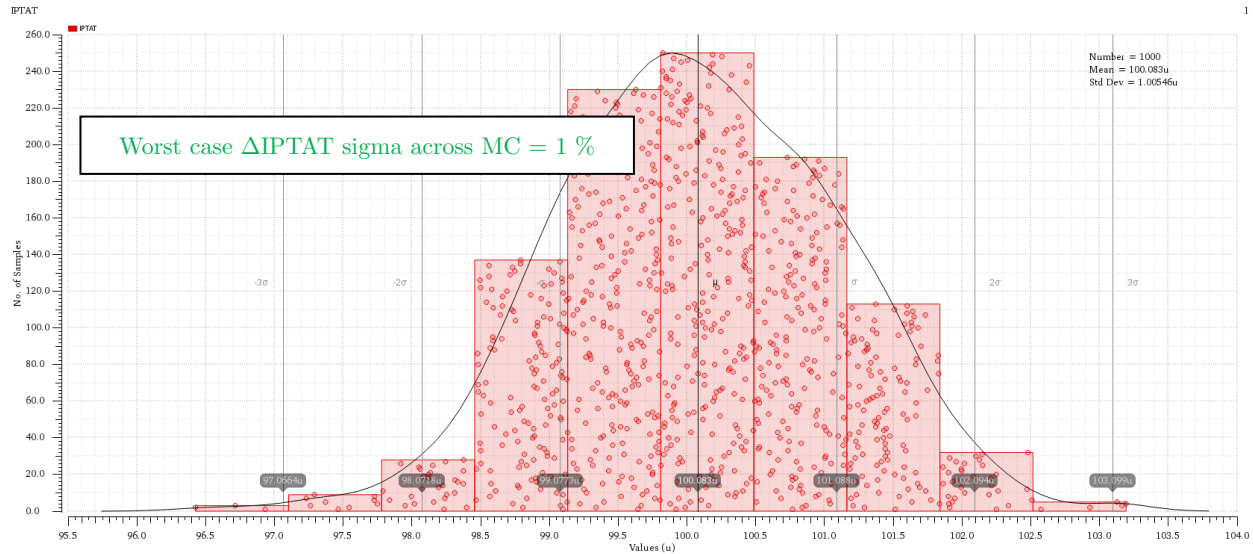


- IPTAT Vs VDD @ Nominal

DC Analysis' dc' VDD = (1.08 -> 1.32)



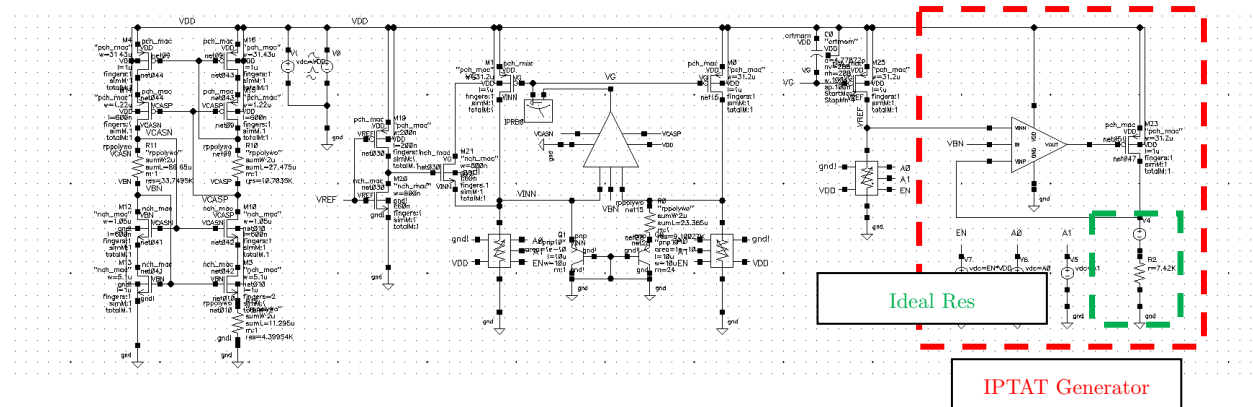
- MC Results



- STB across PVT

Test	Output	Nominal	Spec	Weight	Pass/Fail	Min	Max	FF_0	FF_1	SS_0	SS_1	C3
AnaloglC:BGR:1	/V4/PLUS											
AnaloglC:BGR:1	PMs	69.43				65.13	73.51	65.13	66.76	72.1	73.51	69.39

- Final Circuit



9. Results Summary

Spec.	Target	Units	Achieved	Comments
Temperature range	-40 to +125	C°	-40 to +125	
Supply Variation	-10 to +10	%	-10 to +10	From the nominal supply value
Process Corners	TT, SS, FF		TT, SS, FF	
Nominal VBG Voltage	0.5	V	0.5	
Worst case Δ VBG across Temperature	± 1	%	0.45 %	For TT Corner
Worst case Δ VBG across supply	± 0.5	%	0.32 %	
Worst case Δ VBG	± 3	%	1 %	Across PVT
Worst case Δ VBG sigma across MC	± 1	%	0.92 %	For TT Corner
Nominal IPTAT Current	100	μ A	100	@ 25°, Across PV
IPTAT Slope accuracy	--	%	--	Across PVT and 4 Setting
IPTAT Slope step	-12.5	%	-12.5	Across PVT
IPTAT Min Slope	-50	%	-50	Across PVT
Worst case Δ IPTAT across supply	± 1		0.26	
Worst case Δ IPTAT	± 3		0.55	Across PVT
Worst case Δ VBG sigma across MC	± 1		1	For TT Corner
loop PMs	> 60°	Deg	> 65°	Across PVT
Startup Current	--	μ A	0.5	Across PVT
Supply voltage	1.2	V	1.2	
Power consumption	--	mW	0.267	